SHEET 1 OF 1

| FORM PTO - 1449 | | | | | ATTORNEY DOCKET NO.: ASC-049C1 | | | | | | |
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| SUPPLEMENTAL INFORMATION | | | | | APPLICANT(S): Fit | | | tzgerald | | | |
| DISCLOSURE STATEMENT | | | | | SERIAL NO.: | | 10/ | 10/774,890 | | | |
| • | | | | | | FILING DATE: | | | ebruary 9, 2004 | | |
| | | | | | | GROUP: 28 | | | 18 | | |
| U.S. PATENT DOCUMENTS | | | | | | | | | | | |
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